



FEATURES

- Circular active area
- Ideal for electron detection
- 100% internal QE
- High speed
- Hole in center of detector

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	Ø9mm		63		mm ²
Responsivity, \mathcal{R}	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	160			Volts
Capacitance, C	$V_R = 0V$		1		nF
Capacitance, C	$V_R = 150V$		85		pF
Rise Time	$V_R = 150V, R_L = 50\Omega$			2	nsec
Dark Current	$V_R = 150V$			100	nA

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ²	-10° TO 40°C
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature ¹	260°C

¹0.08" from case for 10 seconds.

²Temperatures exceeding these parameters may create Oxide growth on the active area. Over time Responsivity to Low energy radiation and wavelengths below 150nm will Be Compromised.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

